



2SC4467

NPN EPITAXIAL SILICON TRANSISTOR

SILICON NPN TRIPLE DIFFUSED PLANAR TRANSISTOR

DESCRIPTION

The UTC **2SC4467** is a silicon NPN triple diffused planar transistor, it uses UTC's advanced technology to provide the customers with high DC current gain and high collector-base breakdown voltage, etc.

The UTC **2SC4467** is suitable for audio and general purpose, etc.

FEATURES

- * High DC current gain
- * High collector-base breakdown voltage

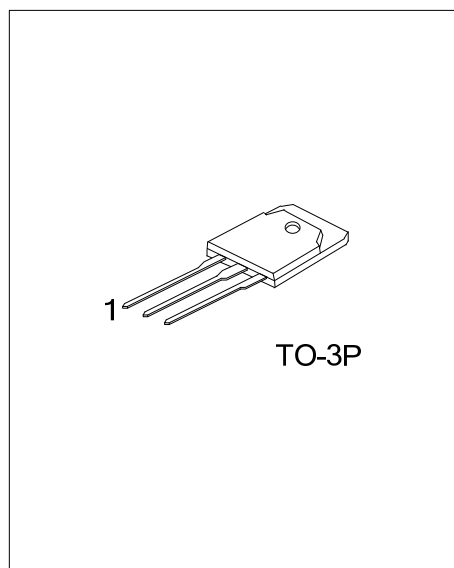
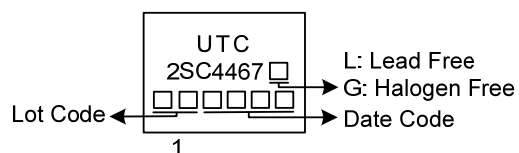
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC4467L-x-T3P-T	2SC4467G-x-T3P-T	TO-3P	B	C	E	Tube

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>2SC4467G-x-T3P-T</p> <ul style="list-style-type: none">(1) Packing Type(2) Package Type(3) Rank(4) Green Package	<ul style="list-style-type: none">(1) T: Tube(2) T3P: TO-3P(3) x: reference to Classification of h_{FE}(4) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	160	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	8	A
Base Current	I_B	3	A
Collector Power Dissipation ($T_C=25^\circ\text{C}$)	P_C	80	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

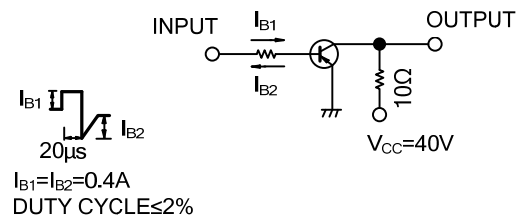
■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I_{CBO}	$V_{CB}=160\text{V}$			10	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=6\text{V}$			10	μA
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=50\text{mA}$	120			V
DC Current Gain	h_{FE}	$V_{CE}=4\text{V}$, $I_C=3\text{A}$	50			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=3\text{A}$, $I_B=0.3\text{A}$			1.5	V
Current Gain Bandwidth Product	f_T	$V_{CE}=12\text{V}$, $I_E=-0.5\text{A}$		20		MHz
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}$, $f=1\text{MHz}$		200		pF
Switching time	Turn-on time	$V_{CC}=40\text{V}$, $R_L=10\Omega$, $I_C=4\text{A}$, $I_{B1}=0.4\text{A}$ $I_{B2}=0.4\text{A}$		0.13		μS
	Storage time			3.50		μS
	Fall time			0.32		μS

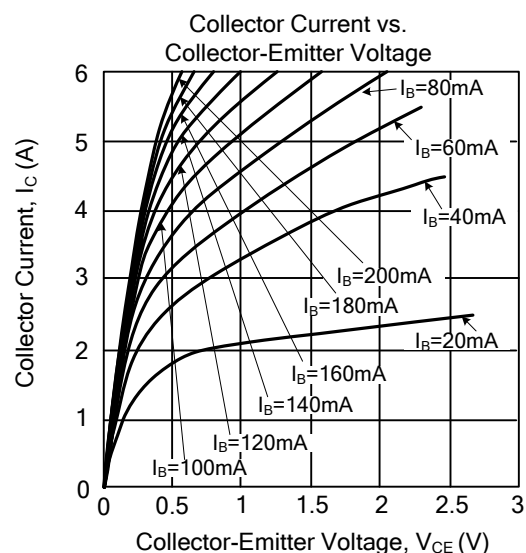
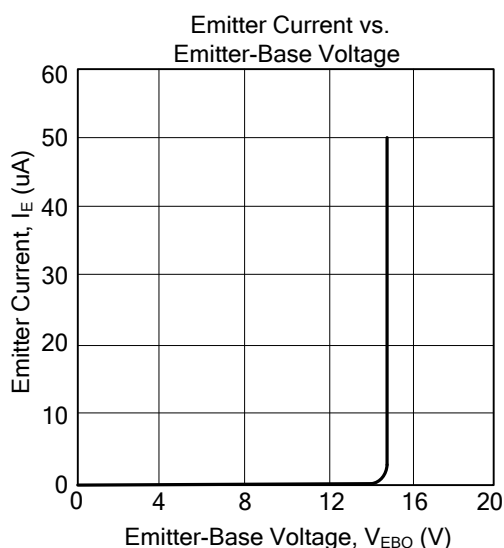
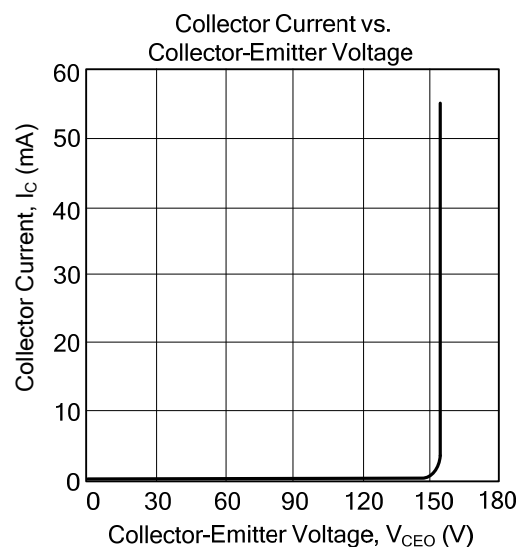
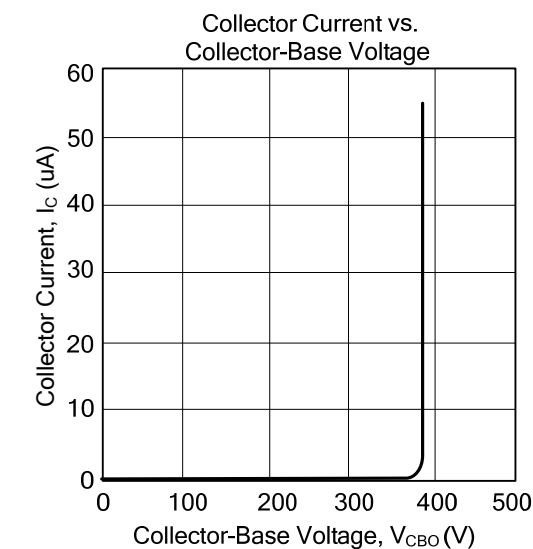
■ CLASSIFICATION OF h_{FE}

RANK	O	P	Y
RANGE	50~100	70~140	90~180

■ TEST CIRCUIT



TYPICAL CHARACTERISTICS



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